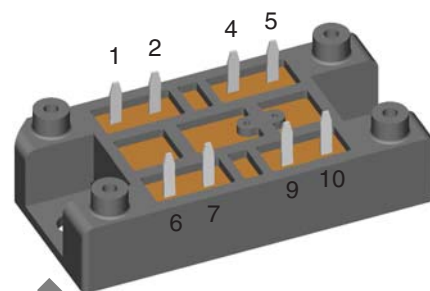
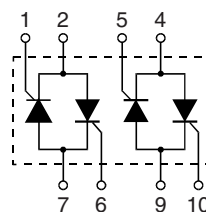


AC Controller Modules

$$I_{RMS} = 2 \times 30 \text{ A}$$

$$V_{RRM} = 1200-1600 \text{ V}$$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
1200	1200	VW2x30-12io1
1400	1400	VW2x30-14io1
1600	1600	VW2x30-16io1



Symbol	Conditions	Maximum Ratings	
I_{RMS}	$T_C = 85^\circ\text{C}$; (per phase)	30	A
I_{TRMS}	$T_{VJ} = T_{VJM}$	22	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; (180° sine ; per thyristor)	14	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ t = 10 ms (50 Hz), sine	200	A
	t = 8.3 ms (60 Hz), sine	210	A
	$T_{VJ} = T_{VJM}$ $V_R = 0$ t = 10 ms (50 Hz), sine	180	A
	t = 8.3 ms (60 Hz), sine	190	A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$ t = 10 ms (50 Hz), sine	200	A ² s
	t = 8.3 ms (60 Hz), sine	190	A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$ t = 10 ms (50 Hz), sine	160	A ² s
	t = 8.3 ms (60 Hz), sine	150	A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200 \mu\text{s}$ $V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.45 \text{ A}$ di _G /dt = 0.45 A/ μs	repetitive, $I_T = 45 \text{ A}$	100 A/ μs
		non repetitive, $I_T = I_{TAVM}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $R_{GK} = \infty$; method 1 (linear voltage rise) $V_{DR} = \frac{2}{3} V_{DRM}$		1000 V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$ $t_p = 30 \mu\text{s}$	10	W
	$t_p = 300 \mu\text{s}$	5	W
P_{GAVM}		0.5	W
V_{RGM}		10	V
T_{VJ}		-40...+125	°C
T_{VJM}		125	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min	3000 V~
		t = 1 s	3600 V~
M_d	Mounting torque (M5)	2-2.5/18-22	Nm/lb.in.
Weight	typ.	35	g

Features

- Thyristor controller for AC (circuit W2C acc. to IEC) for mains frequency
- Soldering connections for PCB mounting
- Isolation voltage 3600 V~
- Planar passivated chips
- UL applied

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Recommended replacement:
VW2x60-12/14/16 io1

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values		
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq$	5	mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.81	V
V_{T0}	For power-loss calculations only		0.8	V
r_T			25	m Ω
V_{GT}	$V_D = 6 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq$ $\leq$	1.5 1.6	V V
I_{GT}	$V_D = 6 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq$ $\leq$	100 200	mA mA
V_{GD}	$T_{VJ} = T_{VJM}$ $V_D = 2/3 V_{DRM}$	$\leq$	0.2	V
I_{GD}		$\leq$	5	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \text{ }\mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	450	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq$	200	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2}V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	2	μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}; t_p = 200 \text{ }\mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = \frac{2}{3}V_{DRM}$	typ.	150	μs
R_{thJC}	per thyristor; DC per module		1.7 0.43	K/W K/W
R_{thJK}	per thyristor; DC per module		2.0 0.5	K/W K/W
d_s	Creeping distance on surface		12.7	mm
d_A	Creepage distance in air		9.4	mm
a	Max. allowable acceleration		50	m/s ²

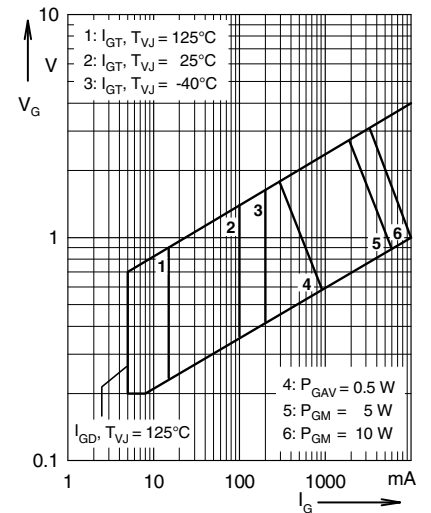


Fig. 1 Gate trigger characteristics

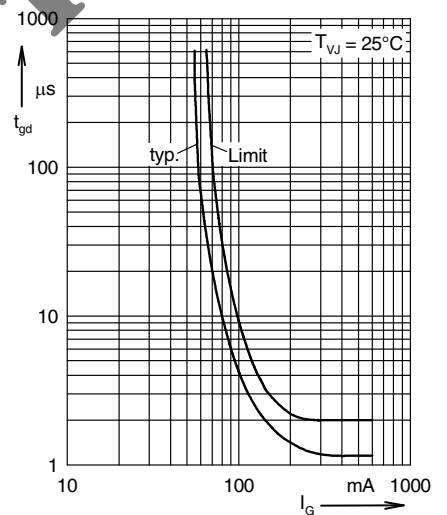


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")

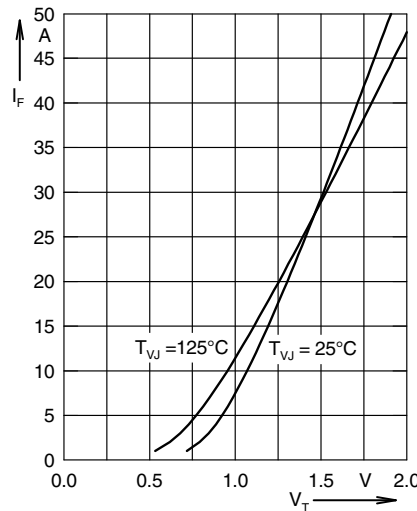
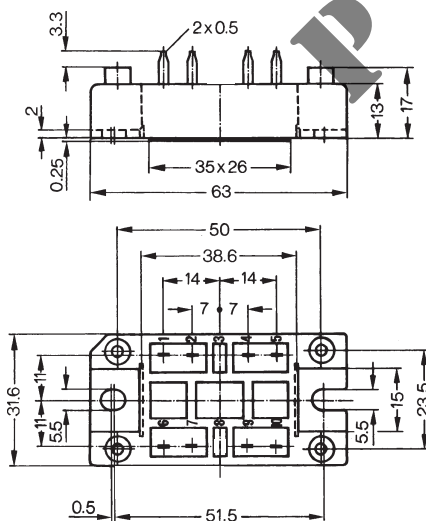


Fig. 3 Forward current vs. voltage drop per leg

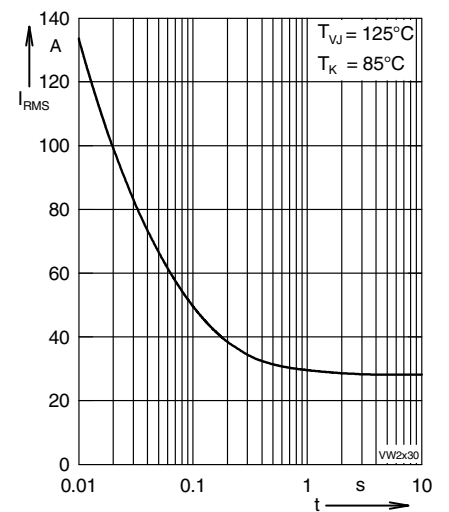


Fig. 4 Rated RMS current vs. time (360° conduction)

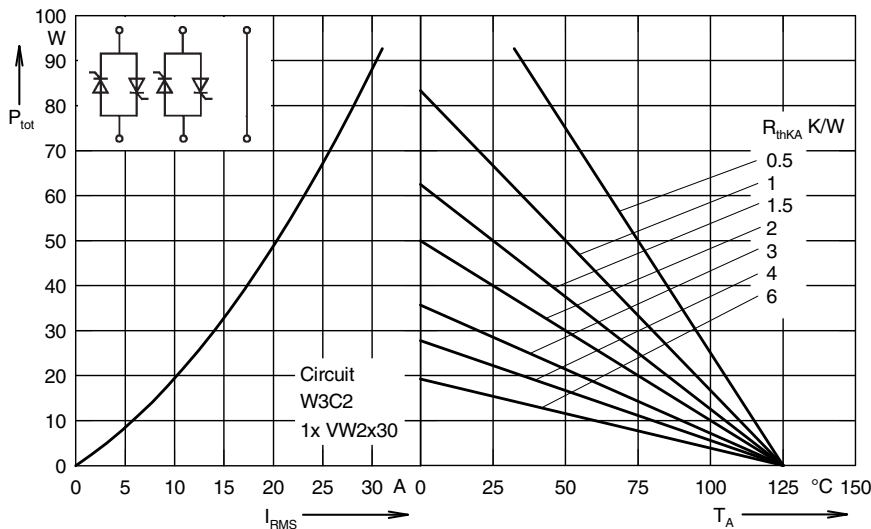


Fig. 5 Load current capability for two phase AC controller

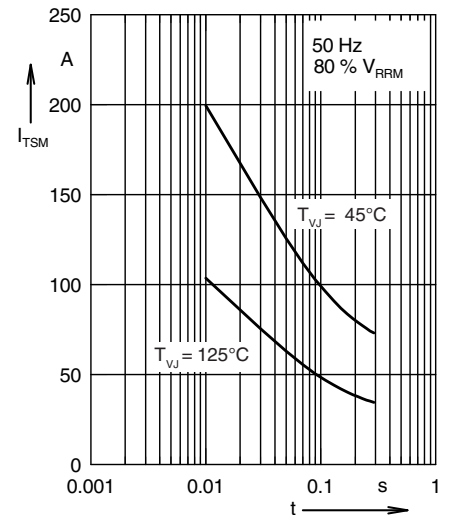


Fig. 6 Surge overload current

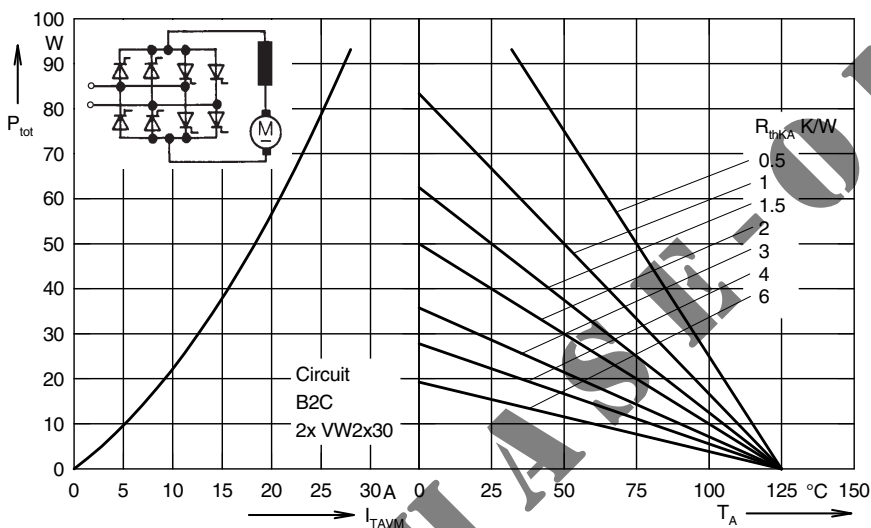


Fig. 7 Power dissipation vs. direct output current and ambient temperature cyclo converter, four quadrant operation

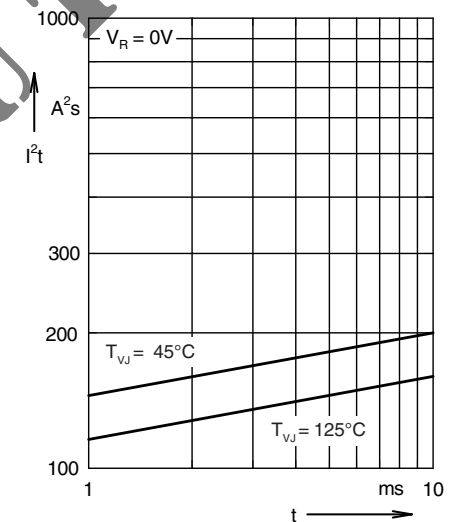


Fig. 8 I^2t vs. time (per thyristor)

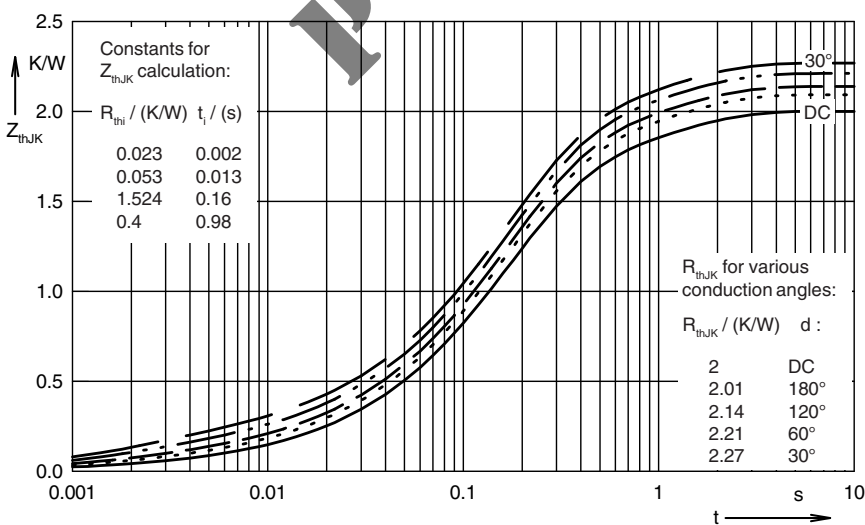


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

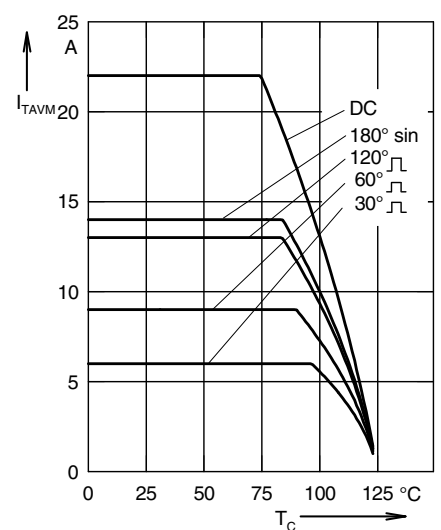


Fig. 10 Maximum forward current at case temperature